Physics FSC Part 2 Chapter 18 Online MCQ's Test

Sr	Questions	Answers Choice
1	A two inputs NAND gat with inputs a and b has an output '0' if.	A. B is zero B. A is zero C. Both A and B are 1 D. Both A and B are '0'
2	For normal transistor the emitter current can be given by	A. I_E = I_C B. I_E = I_C + I_B C. I_E = I_B D. None of these
3	The gate, which changes the logic level to its opposite level is called	A. NOR gate B. AND gate C. OR gate D. NOT gate
4	NAND gate represented by:	A. X = A. B B. X = A+B C. X= A.B D. X=|A+B|
5	When a PN-Junction is reverse biased the depletion region is.	A. Widened B. Narrowed C. Normal D. None of these
6	The circuit of full wave rectification consist of	A. Three diodes B. Four diodes C. Two diodes D. One diode
7	The resistance between the inverting (-) and non inverting inputs is called Input resistance and is the order of.	A. Ohms B. Kilo Ohms C. Mega Ohms D. Thounds Ohms
8	An expression for gain of an inverting amplifier is	C. (R₁R₂) D. None of these
9	X=A+B is the mathematical notation for.	A. OR gate B. NOR gate C. NAND gate D. AND gate
10	The impurity in the germinium is usually in the ratio of	A. 1:10⁶ B. 1:10⁴ C. 1:10⁸ D. 1:10¹⁰
11	A.C. can be converted into D.C. by	A. An oscillator B. Detector C. An amplifier D. Rectifier
12	Most of the electrons in the base of an NPN transistor flow:	A. Out of the base lead B. Into the collector C. Into the emit D. Into the base supply
13	In photovoltaic cell, current is directly proportional to.	A. Wavelength of light B. Intensity of light C. Energy D. Frequency of light
14	_____ is the building block of every electronic circuit.	A. Semi conductor diode B. Resistor C. Capacitor D. Amplifier
15	The ratio of potential barriers of Ge to Si at room temperatrue is.	A. 7:3 B. 1:3 C. 2:5 D. 3:7

16	Which diode works at reverse biasing.	A. LED B. Photo voltaic cell C. Photo diode D. Silicon diode
17	Pulsating output of full wave rectifier can be made smooth by using circuit called.	A. Filter B. Amplifier C. Resistor D. Transistor
18	The average gap for Germanium at 0K is	A. 1.12 ev B. 0.02 ev C. 6.72 ev D. 7.2 ev
19	Base of transistor is of order:	A. 10⁻¹¹m B. 10⁶m C. 10⁻⁸m D. 10⁻⁶m
20	The potential difference across the depletion region of germanium is.	A. 0.3 V B. 0.5 V C. 0.7 V D. 0.8 V